

In the Specification

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For a better understanding of the invention, and to show how embodiments of the same may be carried into effect, reference will now be made, by way of example, to the accompanying diagrammatic drawings, ~~in which Figures 1 to 3 have already been mentioned above and~~, in which:

Figures 1a and 1b show the structure of a cathode plane;

Figure 2a shows a typical structure of an emitter;

Figure 2b shows an exemplary case where an emitter with 2 micron particles is used in an 8 micron diameter emitter cell fabricated in a nominal 4 micron thick gate insulator;

Figure 2c shows an occurrence in which a large particle and its associated insulator coating disrupt a gate structure to form two potential emitting sites;

Figure 3a to 3c illustrate a technique that involves forming a gated structure with a gate electrode deposited on a silicon dioxide layer that is grown on a conducting silicon substrate;

Figures 4a to 4e illustrate steps in one example of a method of creating a broad area field electron emitter;

Figures 5a to 5c illustrate steps in another example of a method of creating a broad area field electron emitter;

Figures 6a to 6c illustrate steps in yet another example of a method of creating a broad area field electron emitter; and

Figures 7a to 7c illustrate examples of devices that utilise examples of broad area field electron emitters.